

IN THE CLAIMS:

Please amend claim 1 as follows:

1. (Amended) A semiconductor device comprising:
metal interconnects made from a multi-layer film composed of a first metal film
deposited on a semiconductor substrate with an insulating film sandwiched therebetween and a
second metal film deposited on said first metal film, wherein the second metal film is a seed layer;
an interlayer insulating film formed over said metal interconnects; and
a plug made from a third metal film provided within a via hole formed in said interlayer insulating film,
wherein said third metal film is selectively grown on said second metal film contacted with a bottom of said via hole.

Please add new claims 12 and 13 as follows:

12. (New) The semiconductor device of Claim 1,
wherein said multi-layer film consists of two layers of said first metal film and said second metal film.
13. (New) The semiconductor device of Claim 5,
wherein the width of said air gap is substantially equal to the space between said metal interconnects.